# **Complementary Silicon Plastic Power Transistors**

... designed for use in general purpose amplifier and switching applications. Compact TO-220 AB package.

## **MAXIMUM RATINGS**

Rating	Symbol	TIP29B TIP30B	TIP29C TIP30C	Unit
Collector-Emitter Voltage	VCEO	80	100	Vdc
Collector-Base Voltage	VCB	80	100	Vdc
Emitter-Base Voltage	VEB	5.0		Vdc
Collector Current — Continuous Peak	lC	1.0 3.0		Adc
Base Current	ΙΒ	0.4		Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	30 0.24		Watts W/°C
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	2.0 0.016		Watts W/°C
Unclamped Inductive Load Energy (See Note 3)	E	32		mJ
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	−65 tc	+150	°C

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction to Case	R <sub>0</sub> JC	4.167	°C/W

NPN TIP29B

TIP29C PNP TIP30B

TIP30C

1 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
80-100 VOLTS
30 WATTS



ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	COM	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	0750				
Collector–Emitter Sustaining Voltage (1) (IC = 30 mAdc, I <sub>B</sub> = 0)	TIP29B, TIP30B TIP29C, TIP30C	VCEO(sus)	80 100	_	Vdc
Collector Cutoff Current (VCE = 60 Vdc, IB	= 0)	ICEO	_	0.3	mAdc
Collector Cutoff Current (VCE = 80 Vdc, VEB = 0) (VCE = 100 Vdc, VEB = 0)	TIP29B, TIP30B TIP29C, TIP30C	ICES		200 200	μAdc
Emitter Cutoff Current (VBE = 5.0 Vdc, IC =	: 0)	IEBO	-	1.0	mAdc
ON CHARACTERISTICS (1)	-7 FM 27	((0)			
DC Current Gain (I <sub>C</sub> = 0.2 Adc, V <sub>CE</sub> = 4.0 (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 4.0		hFE	40 15	— 75	_
Collector-Emitter Saturation Voltage (IC = 1	I.0 Adc, I <sub>B</sub> = 125 mAdc)	VCE(sat)	_	0.7	Vdc
Base-Emitter On Voltage (IC = 1.0 Adc, VC	E = 4.0 Vdc)	V <sub>BE(on)</sub>	_	1.3	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain — Bandwidth Product (2) (IC = 200 mAdc, VCE = 10 Vdc, f <sub>test</sub> = 1	0 MHz)	fT	3.0	_	MHz
Small-Signal Current Gain (I <sub>C</sub> = 0.2 Adc, V	CE = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	20	_	_

(1) Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

(2)  $\Gamma = \ln_{fe} | \bullet | ftest$ . (3) This rating based on testing with  $L_C = 20$  mH,  $R_{BE} = 100 \Omega$ ,  $V_{CC} = 10$  V,  $I_C = 1.8$  A, P.R.F = 10 Hz. REV 1 com



### TIP29B TIP29C TIP30B TIP30C

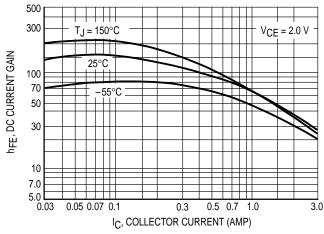


Figure 1. DC Current Gain

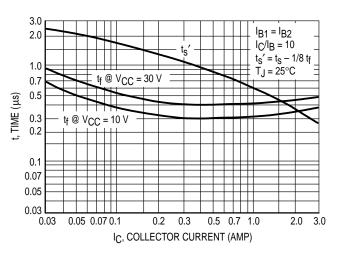


Figure 2. Turn-Off Time

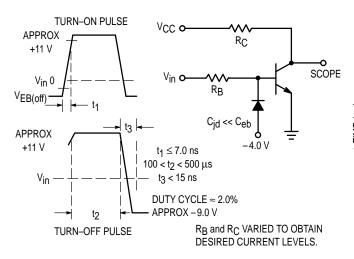


Figure 3. Switching Time Equivalent Circuit

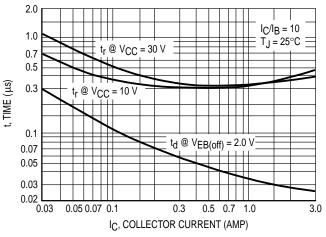


Figure 4. Turn-On Time

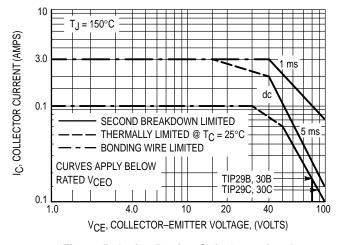


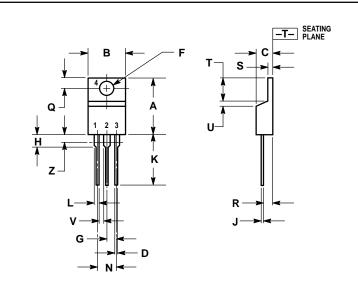
Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# TIP29B TIP29C TIP30B TIP30C

# **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

**CASE 221A-06** TO-220AB **ISSUE Y** 

### TIP29B TIP29C TIP30B TIP30C

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